

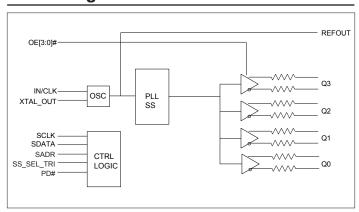


4-Output PCle Gen 6 Clock Generator For Automotive Applications

Description

The DIODES PI6CG334Q is a 4-output very-low-power PCIe® Gen 1/Gen 2/Gen 3/Gen 4/Gen 5/Gen 6 clock generator. It uses 25MHz crystal or CMOS reference as an input to generate the 100MHz low-power differential HCSL outputs with on-chip terminations. The on-chip termination can save 16 external resistors and make layout easier. An additional buffered reference output is provided to serve as a low-noise reference for other circuitry. It uses Diodes' proprietary PLL design to achieve very-low jitter that meets PCIe Gen 1/Gen 2/Gen 3/Gen 4/Gen 5/Gen 6 requirements. It also provides various options such as different slew rate and amplitude through SMBUS, so users can configure the device easily to get the optimized performance for their individual boards. The device also supports selectable spread-spectrum options to reduce EMI for various applications.

Block Diagram



Features

- 3.3V Supply Voltage
- Crystal/CMOS Input: 25MHz
- Four Differential Low Power HCSL Outputs with On-Chip Termination
- Individual Output Enable
- Reference CMOS Output
- Programmable Slew Rate and Output Amplitude for Each Output
- Differential Outputs Blocked until PLL is Locked
- Selectable 0%, -0.25%, or -0.5% Spread on Differential Outputs
- Strapping Pins or SMBus for Configuration
- Differential Output-To-Output Skew <50ps
- Very-Low Jitter Outputs
 - PCIe 6.0 Common Clock (RMS) Jitter <0.04ps
 - Differential Cycle-To-Cycle Jitter <50ps
- PCIe Gen 1/Gen 2/Gen 3/Gen 4/Gen 5/Gen 6 Compliant
- Support Automotive Grade 2
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The PI6CG334Q is suitable for automotive applications requiring specific change control; this part is AEC-Q100 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

- Packaging (Pb-free & Green):
 - □ 32-Contact, 5mm × 5mm WQFN (ZHW)

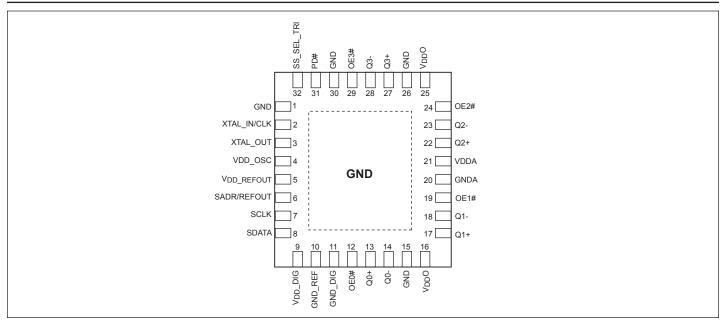
Notes

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q100 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.





Pin Configuration



Pin Description

Pin #	Pin Name	Ту	pe	Description
1, 15, 26, 30	GND	Power		Ground pin
2	XTAL_IN/CLK	Input		Crystal input or CMOS reference input
3	XTAL_OUT	Output		Crystal output
4	V _{DD} _OSC	Power		Power supply for oscillator circuitry, nominal 3.3V
5	V _{DD} _REFOUT	Power		Power supply for buffered CMOS output
6	SADR/REFOUT	Input/ Output	CMOS	Latch to select SMBus Address or LVCMOS REFOUT. This pin has an internal pulldown.
7	SCLK	Input	CMOS	SMBUS clock input, 3.3V tolerant
8	SDATA	Input/ Output	CMOS	SMBUS Data line, 3.3V tolerant
9	V _{DD} _DIG	Power		Power supply for digital circuitry, nominal 3.3V
10	GND_REF	Power		Ground for REFOUT
11	GND_DIG	Power		Ground for digital circuitry
12	OE0#	Input	CMOS	Active low input for enabling Q0 pair. This pin has an internal pull-down. $1 = \text{disable outputs}, 0 = \text{enable outputs}$
13	Q0+	Output	HCSL	Differential true clock output
14	Q0-	Output	HCSL	Differential complementary clock output
16, 25	V _{DDO}	Power		Power supply for differential outputs





Pin #	Pin Name	Ту	pe	Description
17	Q1+	Output	HCSL	Differential true clock output
18	Q1-	Output	HCSL	Differential complementary clock output
19	OE1#	Input	CMOS	Active low input for enabling Q1 pair. This pin has an internal pull-down. 1 = disable outputs, 0 = enable outputs
20	GNDA	Power		Ground for analog circuitry
21	V_{DDA}	Power		Power supply for analog circuitry
22	Q2+	Output	HCSL	Differential true clock output
23	Q2-	Output	HCSL	Differential complementary clock output
24	OE2#	Input	CMOS	Active low input for enabling Q2 pair. This pin has an internal pull-down. 1 = disable outputs, 0 = enable outputs
27	Q3+	Output	HCSL	Differential true clock output
28	Q3-	Output	HCSL	Differential complementary clock output
29	OE3#	Input	CMOS	Active low input for enabling Q3 pair. This pin has an internal pull-down. 1 = disable outputs, 0 = enable outputs
31	PD#	Input	CMOS	Input notifies device to sample latched inputs and start up on first high assertion. Low enters Power Down Mode, subsequent high assertions exit Power Down Mode. This pin has internal pullup resistor.
32	SS_SEL_TRI	Input	Tri-level	Latched select input to select spread-spectrum amount at initial power up. $1 = 0.5\%$ spread, $M = Spread$ off, $0 = Spread$ off. This pin has both internal pull-up and pull-down. Refer to SMBUS byte_1 bit 4, $3 = '01'$ to get -0.25% spread.
Epad	GND	Power		Connect to ground





SMBus Address Selection Table

	SADR	Address	+Read/Write Bit
COLOR COADRA TO A A 10 A COADRA	0	1101000	X
State of SADR on First Application of PD#	1	1101010	X

Power Management Table⁽³⁾

PD#	SMBus OE bit	OEn#	Qn+	Qn-	REFOUT
0	X	X	Low ⁽¹⁾	Low ⁽¹⁾	HiZ ⁽²⁾
1	1	0	Running	Running	Running
1	1	1	Disabled ⁽¹⁾	Disabled ⁽¹⁾	Running
1	0	X	Disabled ⁽¹⁾	Disabled ⁽¹⁾	Disabled ⁽⁴⁾

^{1.} The output state is set by B11[1:0] (Low/Low default).

^{2.} REF is Hi-Z until the 1st assertion of PD# high. After this, when PD# is low, REF is disabled. If Byte3, bit 5 = 1, then REF is running.

^{3.} Input High/ Low defined at default values for device.

^{4.} See SMBUs Byte 3, bit 4.





Maximum Ratings

(Above which useful life may be impaired. For user guidelines, not tested.)

Storage Temperature –65°C to +150°C
Supply Voltage to Ground Potential, V_{DDxx} 0.5V to +4.6V
Input Voltage –0.5V to V_{DD} +0.5V, not exceed 4.6V
SMBus, Input High Voltage
ESD Protection (HBM)
Max Junction Temperature+125°C

Note:

Stresses greater than those listed under MAXIMUM RAT-INGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Operating Conditions

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Тур.	Max.	Units
V _{DDO} , V _{DDA} , V _{DD} OSC, V _{DD} DIG, V _{DD} RE- FOUT	Power Supply Voltage		3.135	3.3	3.465	V
I_{DDA}	Analog Power Supply Current	All outputs active @ 100MHz		22	25	mA
I_{DD}	Power Supply Current	All V_{DD} , except V_{DDA} and V_{DDO} , All outputs active @ 100MHz		17	20	mA
I_{DDO}	IO Power Supply Current ⁽³⁾	V _{DDO} , All outputs active @ 100MHz		27	31	mA
I _{DDA_WL}	Analog Power Supply Wake-on- LAN ⁽¹⁾ Current	Q outputs off, REF output running		0.5	1	mA
I _{DD_WL}	Power Supply Wake-on-LAN ⁽¹⁾ Current	All V _{DD} , except V _{DDA} and V _{DDO} , Q outputs off, REF output running		3	6	mA
I _{DDO_WL}	Power Supply Wake-on-LAN ⁽¹⁾ Current for Outputs	Q outputs off, REF output running		1	2	mA
I _{DDA_PD}	Analog Power Supply Power Down ⁽²⁾ Current	All outputs off		0.5	1	mA
I _{DDO_PD}	IO Power Down ⁽²⁾ Current	All outputs off		1	2	mA
I _{DD_PD}	Power Supply Power Down ⁽²⁾ Current	All outputs off		1	2	mA
T_{A}	Ambient Temperature	Automotive grade	-40		105	°C

- 1. Wake-on-LAN mode: PD# = '0' Byte 3, bit 5 = '1'.
- 2. Power down mode: PD# = '0' Byte 3, bit 5 = '0'.
- 3. Outputs drive 5 inch trace.





Input Electrical Characteristics

Symbol	Parameters	Conditions	Min.	Тур.	Max.	Units
R _{pu}	Internal Pullup Resistance			120		ΚΩ
R _{dn}	Internal Pulldown Resistance			120		ΚΩ
C_{XTAL}	Internal Capacitance on X_IN and X_OUT pins			8		pF
L _{PIN}	Pin Inductance				7	nН

Crystal Characteristic

Parameters	Description	Min.	Тур	Max.	Units
OSCmode	Mode of Oscillation	Fundamental			
FREQ	Frequency		25		MHz
ESR ⁽¹⁾	Equivalent Series Resistance			50	Ω
Cload	Load Capacitance		8		pF
Cshunt	Shunt Capacitance			7	pF
_	Drive Level			200	μW

Note:

SMBus Electrical Characteristics

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions.

Symbol	Parameters	Conditions	Min.	Тур.	Max.	Units
V _{DDSMB}	Nominal Bus Voltage		2.7		3.6	V
		SMBus, $V_{DDSMB} = 3.3V$	2.1		3.6	
V _{IHSMB}	SMBus Input High Voltage	SMBus, V _{DDSMB} < 3.3V	0.65 V _{DDSMB}			V
17	SMBus Input Low Voltage	SMBus, $V_{DDSMB} = 3.3V$			0.8	V
V _{ILSMB}		SMBus, V _{DDSMB} < 3.3V			0.8	
I _{SMBSINK}	SMBus Sink Current	SMBus, at V _{OLSMB}	4			mA
V _{OLSMB}	SMBus Output Low Voltage	SMBus, at I _{SMBSINK}			0.4	V
f _{MAXSMB}	SMBus Operating Frequency	Maximum frequency			500	kHz
t _{RMSB}	SMBus Rise Time	(Max V_{IL} - 0.15) to (Min V_{IH} + 0.15)			1000	ns
t _{FMSB}	SMBus Fall Time	(Min V_{IH} + 0.15) to (Max V_{IL} - 0.15)			300	ns

^{1.} ESR value is dependent upon frequency of oscillation.





Spread Spectrum Characteristic

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions.

Symbol	Parameters	Conditions	Min.	Тур.	Max.	Units
f_{MOD}	SS Modulation Frequency	Triangular modulation	30	31.8	33	kHz

LVCMOS DC Electrical Characteristics

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Тур.	Max.	Units
V _{IH}	Input High Voltage	Single-ended inputs, except SMBus	0.75 V _{DD}		V _{DD} +0.3	V
V_{IM}	Input Mid Voltage	SS_SEL_TRI	$0.4 V_{ m DD}$	$0.5 V_{ m DD}$	$0.6 V_{ m DD}$	V
V_{IL}	Input Low Voltage	Single-ended inputs, except SMBus	-0.3		0.25 V _{DD}	V
I_{IH}	Input High Current	Single-ended inputs, $V_{IN} = V_{DD}$			5	μΑ
I_{IL}	Input Low Current	Single-ended inputs, $V_{IN} = 0V$	-5			μΑ
I_{IH}	Input High Current	Single-ended inputs with pullup/pulldown resistor, $V_{\rm IN} = V_{\rm DD}$			50	μΑ
I_{IL}	Input Low Current	Single-ended inputs with pullup/pulldown resistor, $V_{\rm IN} = 0V$	-50			μA
V _{OH}	Output High Voltage	REFOUT, except SMBus; $I_{OH} = -2mA$	$0.8 \times V_{\mathrm{DD}_{-}}$			V
V _{OL}	Output Low Voltage	REFOUT, except SMBus; $I_{OL} = 2mA$			$0.2 \times V_{DD_}$	V
R _{OUT}	CMOS Output Impedance			20		Ω
C _{IN}	Input Capacitance		1.5		5	pF

LVCMOS AC Characteristics

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Тур.	Max.	Units
f _{INPUT}	Input Frequency	XTAL_IN/CLK		25		MHz
t _{RIN}	Input Rise Time	Single-ended inputs			5	ns
t _{FIN}	Input Fall Time	Single-ended inputs			5	ns
t _{STAB}	Clock Stabilization	From power up and after input clock stabilization or deassertion of PD# to first clock		0.75	1	ms
t _{OELAT}	Output Enable Latency	Q start after OE# assertion Q stop after OE# deassertion	1		3	clocks





Symbol	Parameters	Conditions	Min.	Тур.	Max.	Units
t _{PDLAT}	PD# Deassertion	Differential outputs enable after PD# deassertion		20	300	μs
t _{PERIOD}	REFOUT Clock Period	UT Clock Period REFOUT, assume input is at 25MHz		40		ns
f_{ACC}	REFOUT Frequency Accuracy ⁽¹⁾	REFOUT, long term accuracy to input		0		ppm
		Byte 3 = 1F, 20% to 80% of V _{DDREF}	0.8	1.4	2	V/ns
	DEFOLIT (I D ((I)	Byte 3 = 5F, 20% to 80% of V _{DDREF}	1.5	2.4	3.2	V/ns
$t_{ m SLEW}$	REFOUT Slew Rate ⁽¹⁾	Byte 3 = 9F, 20% to 80% of V _{DDREF}	2.0	3.0	3.9	V/ns
		Byte 3 = DF, 20% to 80% of V _{DDREF}	2.3	3.2	4.5	V/ns
t _{DC}	REFOUT Duty Cycle ⁽¹⁾	$V_T = V_{\rm DD}$ /2V, driven by a Xtal	45	50	55	%
t _{DCDIS}	REFOUT Duty Cycle Distortion	$V_T = V_{DD}$ /2V, driven by an external source	-2	0	+2	%
t _{JITCC}	REFOUT Cycle-Cycle Jitter	$V_T = V_{\rm DD}$ /2V, driven by a Xtal		70	150	ps
,	DEFOLIE DI 1144 DAGO	12kHz to 5MHz, SSC off, driven by a Xtal		0.16	0.3	ps
tлтрн	REFOUT Phase Jitter, RMS	12kHz to 5MHz, SSC on, driven by a Xtal		0.9	1.5	ps
,	M. Di	1kHz offset, driven by a Xtal		-149	-135	dBc/Hz
t _{JITN}	Noise Floor	10kHz offset to Nyquist, driven by a Xtal		-158	-140	dBc/Hz

Note:

HCSL Output Characteristics

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Condition	Min.	Тур.	Max.	Units
V _{OH}	Output Voltage High ⁽¹⁾	Statistical measurement on single-ended	660	784	850	mV
V _{OL}	Output Voltage Low ⁽¹⁾	signal using oscilloscope math function			150	mV
V _{OMAX}	Output Voltage Maximum ⁽¹⁾	Measurement on single ended signal using		816	1150	mV
V _{OMIN}	Output Voltage Minimum ⁽¹⁾	absolute value	-300	-42		mV
V _{OC}	Output Cross Voltage ^(1,2,4)		250	430	550	mV
DV _{OC}	V _{OC} Magnitude Change ^(1,2,5)			12	140	mV

- 1. At default SMBUS amplitude settings.
- 2. Guaranteed by design and characterization—not 100% tested in production.
- 3. Measured from differential waveform.
- $4. \ \, This one is defined as voltage where Q+=Q-\ measured on a component test board and only applied to the differential rising edge.$
- 5. The total variation of all Vcross measurements in any particular system. This is a subset of Vcross_min/max allowed.

^{1.} Guaranteed by design and characterization—not 100% tested in production.





HCSL Output AC Characteristics

Temperature = T_A ; Supply voltages per normal operation conditions; See test circuits for the load conditions.

Symbol	Parameters	Condition	Min.	Тур.	Max.	Spec Limit	Units
f _{OUT}	Output Frequency			100			MHz
4	Slew Rate ^(1,2,3)	Scope averaging on fast setting	2.5	3.2	4		V/ns
t_{RF}	Siew Rate.	Scope averaging on slow setting	2.2	3	3.7		V/ns
Dt_{RF}	Slew Rate Matching ^(1,2,4)	Scope averaging on		7	15		%
t_{DC}	Duty Cycle ^(1,2)	Measured differentially, PLL Mode	45	50	55		%
t _{SKEW}	Output Skew ^(1,2)	Averaging on, $V_T = 50\%$		20	50		ps
tj _{c-c}	Cycle-to-Cycle Jitter ^(1,2)			20	50		ps
		PCIe 1.0 ⁽⁶⁾ (2.5 Gb/s)		20	30	86	ps(p-p)
	Integrated Phase Jitter (RMS)	PCIe 2.0 (5 Gb/s)		0.5	0.6	3.1	ps
		PCIe 3.0 (8 Gb/s)		0.32	0.42	1.0	ps
tj _{PHASE}	(1,5)	PCIe 4.0 (16 Gb/s)		0.32	0.4	0.5	ps
		PCIe 5.0 (32 Gb/s)		0.05	0.06	0.15	ps
		PCIe 6.0 (64Gb/s)		0.03	0.04	0.1	ps
tj _{PH-SRISG2}	Integrated Phase Jitter (RMS)	PCIe 2.0 (5 Gb/s)		0.6	0.92	N/A	ps
tj _{PH-SRISG3}	Integrated Phase Jitter (RMS)	PCIe 3.0 (8 Gb/s)		0.5	0.6	N/A	ps
tj _{PH-SRISG4}	Integrated Phase Jitter (RMS)	PCIe 4.0 (16 Gb/s)		0.4	0.5	N/A	ps
tj _{PH-SRISG5}	Integrated Phase Jitter (RMS)	PCIe 5.0 (32 Gb/s)		0.06	0.07	N/A	ps
tj _{PH-SRISG6}	Integrated Phase Jitter (RMS)	PCIe 6.0 (64Gb/s)		0.04	0.05	N/A	ps

- 1. Guaranteed by design and characterization—not 100% tested in production.
- 2. Measured from differential waveform.
- $3. \ \ Slew\ rate\ is\ measured\ through\ the\ Vswing\ voltage\ range\ centered\ around\ differential\ 0V,\ within\ \pm 150mV\ window.$
- 4. It is measured using a ± 75 mV window centered on the average cross point.
- 5. See http://www.pcisig.com for complete specs.
- 6. Sample size of at least 100k cycles. This can be extrapolated to 108ps pk-pk @ 1M cycles for a BER of 10^{-12} .





SMBus Serial Data Interface

The PI6CG334Q is a slave-only device that supports block read and block write protocol using a single 7-bit address and read/write bit as shown below.

Read and write block transfers can be stopped after any complete byte transfer.

Address Assignment

A6	A5	A4	A3	A2	A1	A0	R/W
1	1	0	1	0	SADR	0	1/0

Note:

 $1. \ SMB us \ address \ is \ latched \ on \ SADR \ pin.$

How to Write

1 bit	7 bits	1 bit	1 bit	8 bits	1 bit	8 bits	1 bit	8 bits	1 bit	8 bits	1 bit	1 bit
Start bit	Add.	W(0)	Ack	Beginning Byte loca- tion = N	Ack	Data Byte count = X	Ack	Beginning Data Byte (N)	Ack	 Data Byte (N+X-1)	Ack	Stop bit

How to Read

1 bit	7 bits	1 bit	1 bit	8 bits	1 bit	1 bit	7 bits	1 bit	1 bit	8 bits	1 bit	8 bits	1 bit
Start bit	Address	W(0)	Ack	Beginning Byte loca- tion = N	Ack	Repeat Start bit	Address	R(1)	Ack	Data Byte count = X	Ack	Beginning Data Byte (N)	Ack

	8 bits	1 bit	1 bit
	Data Byte	NAck	Stop bit
	(N+X-1)	NACK	Stop bit

Byte 0	Byte 0: Output Enable Register										
Bit	Control Function	Description	Туре	Power-up Condition	0	1					
7	Reserved	_	_	1		_					
6	Q3_OE	Q3 output enable	RW	1		Pin Control					
5	Q2_OE	Q2 output enable	RW	1		Pin Control					
4	Reserved	_	_	1	Can D11[1.0]	_					
3	Q1_OE	Q1 output enable	RW	1	See B11[1:0]	Pin Control					
2	Reserved	_	_	1		_					
1	Q0_OE	Q0 output enable	RW	1		Pin Control					
0	Reserved	_	_	1		_					

Note:

Downloaded from Arrow.com.

1. A low on these bits will override the OE# pins and force the differential outputs to the state indicated by B11[1:0] (Low/ Low default).





Byte	Byte 1: SS Spread Spectrum and Control Register									
Bit	Control Function	Description	Туре	Power-up Condition	0	1				
7	SSENRB1	SS Enable Readback Bit1	R	Latch	'00' for SS_SEL	_TRI = '0',				
6	SSENRB0	SS Enable Readback Bit0	R	Latch	'10' for SS_SEL_ for SS_SEL_TR					
5	SSEN_SWCTR	Enable SW control of SS	RW	0	Values in B1[7:6] control SS amount	Values in B1[4:3] control SS amount				
4	SSENSW1	SS enable SW control Bit1	RW ⁽¹⁾	0	'00' = SS off, '01	' = -0.25% SS,				
3	SSENSW0	SS enable SW control Bit0	RW ⁽¹⁾	0	'10' = SS off, '11'	= -0.5% SS				
2	Reserved	_	_	1	_	_				
1	Amplitude1	Control output amulitudo	RW	1	'00' = 0.6V, '01' =	= 0.68V, '10' =				
0	Amplitude0	Control output amplitude	RW	0	0.75V, '11' = 0.85V					

^{1.} Spread must be selected OFF or ON with the hardware latch pin. These bits must not be used to turn spread ON or OFF after power up. These bits can be used to change the spread amount, and B1[5] must be set to a 1 for these bits to have any effect on the part. If these bits are used to turn spread OFF or ON, the system must be reset.

Byte 2	2: Differential Output S	lew Rate Control Register				
Bit	Control Function	Description	Туре	Power-up Condition	0	1
7	Reserved	_	_	1	_	_
6	SLEWRATECTR_Q3	Control slew rate of Q3	RW	1	Slow setting	Fast setting
5	SLEWRATECTR_Q2	Control slew rate of Q2	RW	1	Slow setting	Fast setting
4	Reserved	_	_	1	_	_
3	SLEWRATECTR_Q1	Control slew rate of Q1	RW	1	Slow setting	Fast setting
2	Reserved	_	_	1	_	_
1	SLEWRATECTR_Q0	Control slew rate of Q0	RW	1	Slow setting	Fast setting
0	Reserved	_	_	1	_	_





Byte 3:	Byte 3: REF Control Register										
Bit	Control Function	Description	Туре	Power-up Condition	0	1					
7	DEECLEMD ATE	Class with a sential for DEE	RW	0	'00' = 1.4V/ns '0	01' = 2.4V/ns,					
6	REFSLEWRATE	Slew rate control for REF	RW	1	'10' = 3V/ns, '11' = 3.2V/ns						
5	REF_PDSTATE	Wake-on-Lan enable for REF	RW	0	REF = Dis- abled in PD state ⁽¹⁾	REF = run- ning in PD state					
4	REF_OE	Output enable for REF	RW	1	REF = Dis- abled ⁽¹⁾	REF = run- ning					
3	Reserved	_	_	1	_	_					
2	Reserved	_	_	1	_	_					
1	Reserved	_	_	1	_	_					
0	Reserved	_	_	1	_						

^{1.} The disabled state depends on Byte11[1:0]. '00' = Low, '01' = HiZ, '10' = Low, '11' = High.

Byte 4:	Byte 4: Reserved										
Bit	Control Function	Description	Туре	Power-up Condition	0	1					
7:0	Reserved	_	_	0x40	_	_					
Byte 5:	Revision and Vendor	ID Register									
Bit	Control Function	Description	Туре	Power-up Condition	0	1					
7	RID3		R	0							
6	RID2	Desiring ID	R	0	rev = 0000						
5	RID1	Revision ID	R	0							
4	RID0		R	0							
3	PVID3		R	0							
2	PVID2	W. J. D	R	0	Diodes = 0011						
1	PVID1	Vendor ID	R	1							
0	PVID0		R	1							





B9: 0x00

Byte 6	6: Device Type/Device	ID Register					
Bit	Control Function	Description	Туре	Power-up Condition	0	1	
7	DTYPE1	D : 4	R	0	'00' = CG, '01' =	ZDB,	
6	DTYPE0	Device type	R	0	'10' = Reserve, '	11' = NZDB	
5	DID5		R	0			
4	DID4		R	0			
3	DID3	D : ID	R	1	001000 binary, 08Hex		
2	DID2	Device ID	R	0	001000 binary,	08Hex	
1	DID1		R	0			
0	DID0		R	0			
Byte ?	7: Byte Count Register						
Bit	Control Function	Description	Туре	Power-up Condition	0	1	
7	Reserved	_	_	0	_	_	
6	Reserved	_	_	0	_	_	
5	Reserved	_	_	0	_	_	
4	BC4		RW	0			
3	BC3		RW	1	Writing to this	register will	
2	BC2	Byte count programming	RW	0	configure how	many bytes wil	
1	BC1		RW	0	be read back, d	efault is 8 bytes	
0	BC0		RW	0			
Byte 8	3 and 9: Reserved						
Bit	Control Function	Description	Туре	Power-up Condition	0	1	
7:0	Reserved	_	_	B8: 0x36	_	_	





Byte 10: PD Restore							
Bit	Control Function	Description	Туре	Power-up Condition	0	1	
7	Reserved	_	_	0	_	_	
6	PD Restore	PD Restore to default configuration	RW	1	Clear PD Config	Keep PD Config	
5:0	Reserved	_	_	0	_	_	

Byte 11	Byte 11: Stop Control								
Bit	Control Function	Description	Туре	Power-up Condition	0	1			
7:2	Reserved	_	_	0	_	_			
1	STP1	True/ Compliment DIF Output Disable Sate	RW	0	00= Low/Low	10= High/ Low			
0	STP0		RW	0	01= HiZ/HiZ	11= Low/High			

Byte 1	Byte 12: Impedance Control							
Bit	Control Function	Description	Туре	Power-up Condition	0	1		
7	Q1_Zout1	Q1 Zout	RW					
6	Q1_Zout0	Q1 Zout	RW					
5	Reserved				00 = Reserved			
4	Reserved			10	$01 = 85\Omega$			
3	Q0_Zout1	Q0 Zout	RW	10	$10 = 100\Omega$			
2	Q0_Zout0	Q0 Zout	RW		11 = Reserved			
1	Reserved							
0	Reserved							

Byte 13: Impedance Control							
Bit	Control Function	Description	Туре	Power Up Condition	0	1	
7	Reserved						
6	Reserved						
5	Q3_Zout1	Q3 Zout	RW		00 = Reserved		
4	Q3_Zout0	Q3 Zout	RW	10	$01 = 85\Omega$		
3	Q2_Zout1	Q2 Zout	RW	10	$10 = 100\Omega$		
2	Q2_Zout0	Q2 Zout	RW		11 = Reserved		
1	Reserved						
0	Reserved						





Byte 14: OE Termination Control							
Bit	Control Function	Description	Туре	Power-up Condition	0	1	
7	OE1_term1	OE1 pullup or down	RW	0	00=None	10= Pullup	
6	OE1_term0	OE1 pullup or down	RW	1	01=Pulldown	11=Pullup and Down	
5	Reserved	_	_	0	_	_	
4	Reserved	_	_	1	_	_	
3	OE0_term1	OE0 pullup or down	RW	0	00=None	10= Pullup	
2	OE0_term0	OE0 pullup or down	RW	1	01=Pulldown	11=Pullup and Down	
1	Reserved	_	_	0	_	_	
0	Reserved	_	_	1	_	_	

Byte 1	15: OE Termination Co	ntrol				
Bit	Control Function	Description	Туре	Power-up Condition	0	1
7	Reserved	_	_	0	_	_
6	Reserved	_	_	1	_	_
5	OE3_term1	OE3 pullup or down	RW	0	00=None	10= Pullup
4	OE3_term0	OE3 pullup or down	RW	1	01=Pulldown	11=Pullup and Down
3	OE2_term1	OE2 pullup or down	RW	0	00=None	10= Pullup
2	OE2_term0	OE2 pullup or down	RW	1	01=Pulldown	11=Pullup and Down
1	Reserved	_	_	0	_	_
0	Reserved	_	_	1	_	_

Byte 16: Power Good Termination Control								
Bit	Control Function	Description	Туре	Power-up Condition	0	1		
7:2	Reserved	_	_	0x09	_	_		
1	PWRGD_PD1		RW	1	00=None	10= Pullup		
0	PWRGD_PD0	Clock power good and power-down pullup or pulldown	RW	0	01=Pulldown	11=Pullup and Down		

Byte 17: Reserved





Byte 1	Byte 18: Enable Pin Control							
Bit	Control Function	Description	Туре	Power-up Condition	0	1		
7	Reserved	_	_	0	_	_		
6	OE3_Enable	Sets Enable High or Low	RW	0	Enable = Low	Enable = High		
5	OE2_Enable	Sets Enable High or Low	RW	0	Enable = Low	Enable = High		
4	Reserved	_	_	0	_	_		
3	OE1_Enable	Sets Enable High or Low	RW	0	Enable = Low	Enable = High		
2	Reserved	_	_	0	_	_		
1	OE0_Enable	Sets Enable High or Low	RW	0	Enable = Low	Enable = High		
0	Reserved	_	_	0	_	_		

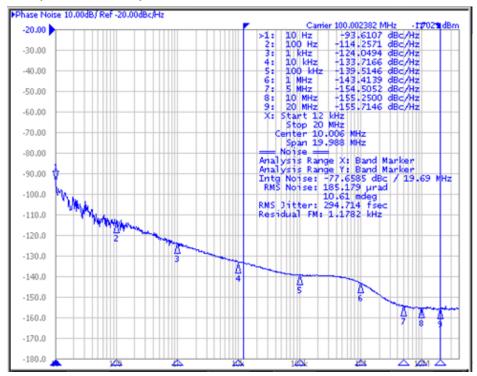
Byte 19: Power Down Pin Control							
Bit	Control Function	Description	Туре	Power-up Condition	0	1	
7:1	Reserved	_	_	0	_	_	
0	PWRGD_PD	PWRGD_PD Active via Pullup or Pulldown	RW	0	Power Down = Low	Power Down = High	



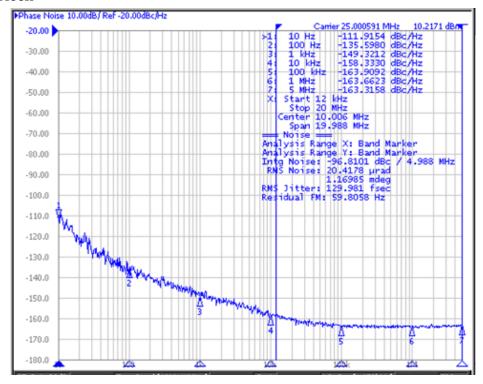


Phase Noise Plots

100MHz HCSL Clock (12k to 20MHz)



25MHz CMOS Clock





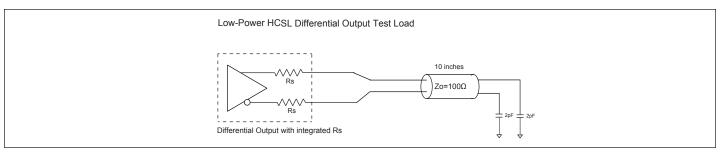


Figure 1. Low Power HCSL Test Circuit

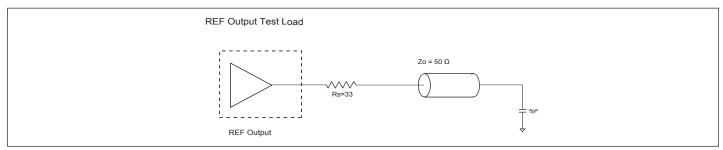


Figure 2. CMOS REF Test Circuit

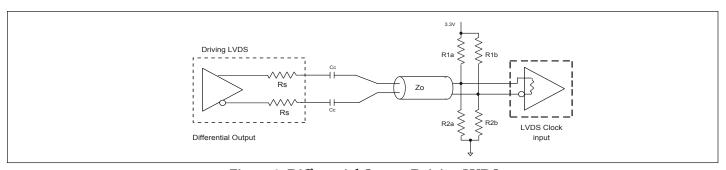


Figure 3. Differential Output Driving LVDS

Alternate Differential Output Terminations

Component	Receiver with Termination	Receiver without Termination	Unit
R _{1a} , R _{1b}	10,000	140	Ω
R _{2a} , R _{2b}	5600	75	Ω
C _C	0.1	0.1	μF
V _{CM}	1.2	1.2	V

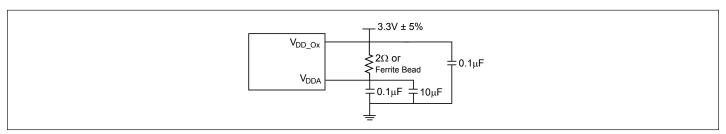


Figure 4. Power Supply Filter

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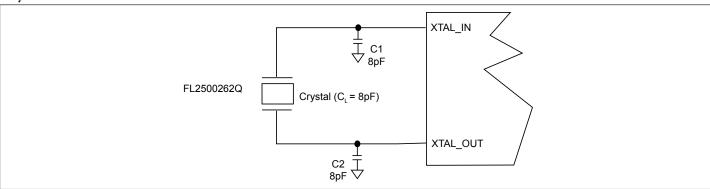




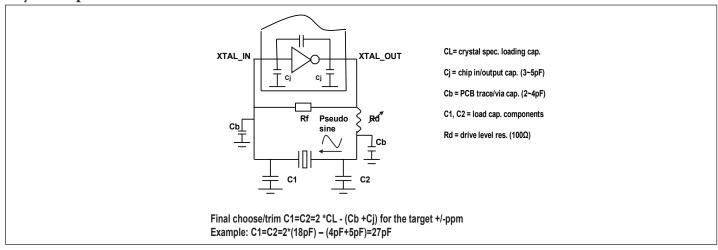
Crystal Circuit Connection

The following diagram shows PI6CG334Q crystal circuit connection with a parallel crystal. For the CL = 8pF crystal, it is suggested to use C1 = 8pF and C2 = 8pF. C1 and C2 can be adjusted to fine tune to the target ppm of crystal oscillator according to different board layouts based on the following formula in the Crystal Capacitor Calculation diagram.

Crystal Oscillator Circuit



Crystal Capacitor Calculation



Recommended Crystal Specification

Diodes Recommends:

- $a)\ FL2500262Q,\ SMD\ 3.2x2.5(4P),\ 25MHz,\ CL=8pF,\ \pm 50ppm,\ https://www.diodes.com/assets/Datasheets/FL.pdf.$
- b) FW2500054Q, SMD 2.0x1.6(4P), 25MHz, CL=8pF, ±50ppm, https://www.diodes.com/assets/Datasheets/FW.pdf.

Thermal Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
θ_{JA}	Thermal Resistance Junction to Ambient	Still air			44.7	°C/W
θ_{JC}	Thermal Resistance Junction to Case				21.7	°C/W





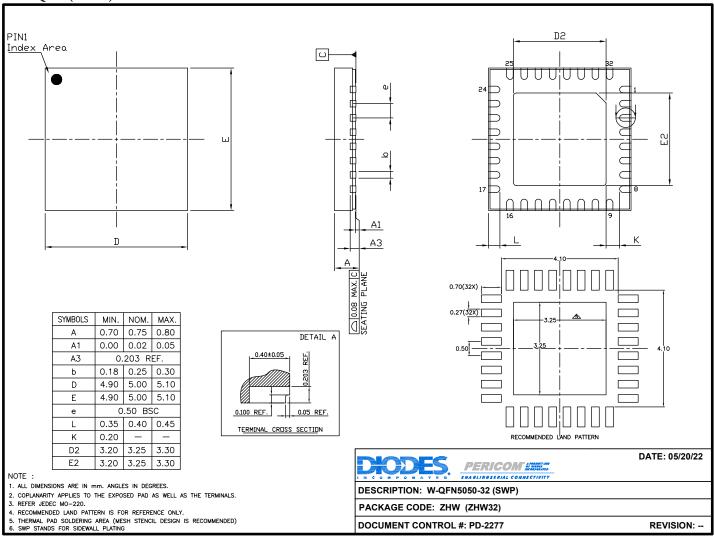
Part Marking		
	PI6CG33 4Q2ZHWE YYWWXX YY: Year WW: Workweek 1st X: Assembly Code 2nd X: Fab Code	





Packaging Mechanical

32-WQFN (ZHW)



For latest package information:

 $See \ http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/.$

Ordering Information

Ordering Code	Package Code	Package Description	Operating Temperature
PI6CG334Q2ZHWEX	ZHW	W-QFN5050-32 (SWP)	-40°C to 105°C

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Q = Automotive Compliant
- 5. 2 = AEC-Q100 Grade Level
- 6. E = Pb-free and Green
- 7. X suffix = Tape/Reel





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